

66-88 MHz RF ASSEMBLY I9D4I6478G8, 9, 14 & 15

AND

MIXER/IF BOARD I9C3274I3GI, 2

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DESCRIPTION

The RF Assembly uses two tuned helical resonators and four L-C tuned circuits to provide front end selectivity.

The Mixer/IF board (MIF) uses the RF input from the RF Assembly and the mixer injection frequency from the oscillator/multiplier board to generate the IF frequency.

through four L-C tuned circuits (L1-C7, L2-C8, L3-C9 and L4-C10) to the mixer. The four tuned circuits and the two helical resonators provide the receiver front end selectivity.

MIXER-IF

MIXER & CRYSTAL FILTER

The mixer uses a FET (Q501) as the active device. The FET mixer provides a high input impedance, high power gain, and an output relatively free of harmonics (low in intermodulation products).

CIRCUIT ANALYSIS

RF ASSEMBLY

ANTENNA INPUT A301A/A301B

An RF signal from the antenna is applied to A301 which provides an AC ground between vehicle ground and receiver A-. Resistor R1 prevents a static charge from building up on the vehicle antenna. The output of A301 is coupled through two high-Q helical resonators (L301, C301 and L302, C302) to the RF amplifier. The coils are tuned to the incoming frequency by C301 and C302. Lamp DS1 protects the RF amplifier stage against an excessive RF input.

RF AMPLIFIER A302

RF Amplifier Q1 is a Field-Effect Transistor (FET). Q1 operates as a grounded gate amplifier, with the RF input applied to the "source" terminal. This method of operation provides a low impedance input to the amplifier. The amplified output is taken from the "drain" terminal and coupled

In the mixer stage, RF from the RF amplifier stage is coupled through tank circuit L501 and C502 to the gate of mixer Q501. The tank circuit provides increased selectivity and impedance matching between the RF Assembly and the gate of mixer Q501. Injection voltage from the multiplier-selectivity stages is inductively coupled through L502 to the source of the mixer. The mixer IF output signal is coupled from the drain of Q501 through a tuned circuit (L505 and C511) which matches the mixer output to the input of the four-pole monolithic crystal filter. The highly-selective crystal filter (FL501 and FL502) provides the first portion of the receiver IF selectivity. The output of the filter is coupled through impedance matching network Z502 (L520 and C523) to the IF amplifier.

IF AMPLIFIER

IF amplifier Q502 is a dual-gate FET. The filter output is applied to Gate 1 of

the amplifier, and the output is taken from the drain. The biasing on Gate 2 and the drain load determines the gain of the stage. The amplifier provides approximately 20 dB of IF gain. The output of Q502 is coupled through a network (L521 and C520) that matches the amplifier output to the crystal filter on the next IF stage. The output of the MIF board is coupled to the next IF stage through feed-through

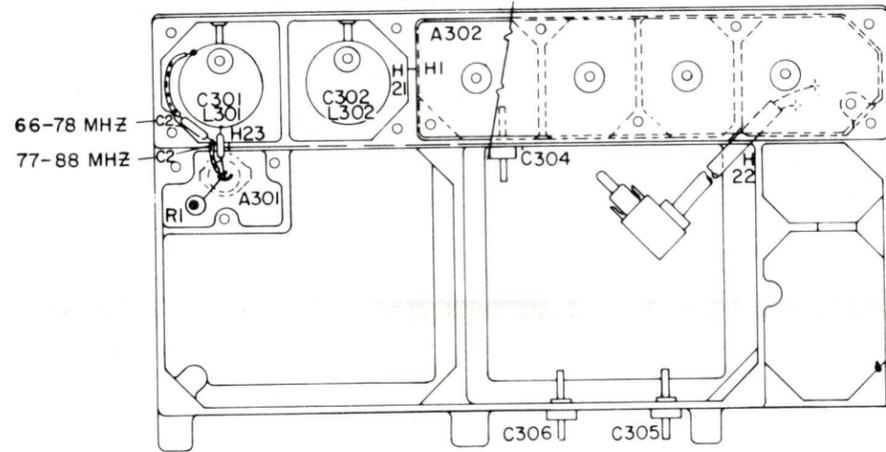
capacitor C305.

Supply voltage for the RF amplifier and MIF board is supplied through feed-through capacitor C306. SERVICE NOTE: Variable capacitor C521 does not require adjustment when performing normal alignment. If the 4-pole monolithic crystal filter is replaced, then adjustment of C521 is necessary for optimum IF response.

GENERAL ELECTRIC COMPANY • MOBILE COMMUNICATIONS DIVISION
WORLD HEADQUARTERS • LYNCHBURG, VIRGINIA 24502 U.S.A.

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**RF ASSEMBLY
BOTTOM VIEW**

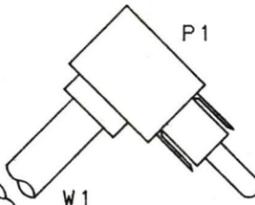


CENTER CONDUCTOR
IN H4 FOR GROUPS 1 THRU 4

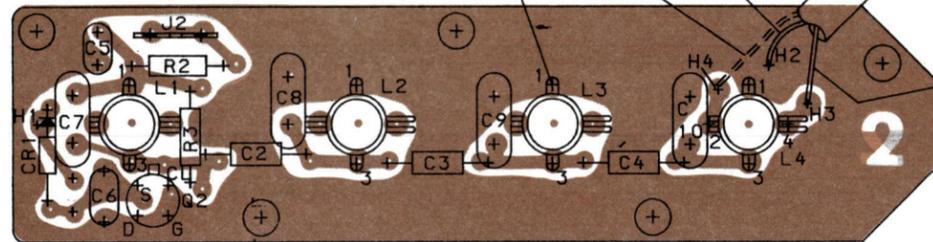
RAISED TAB ON
COIL FORM INDICATES
PIN 1 ON L1 - L4

TWISTED
SHIELD

**A302
RF PRE-SELECTOR**

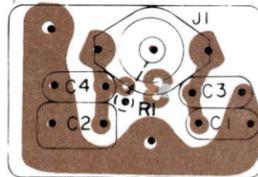


CENTER CONDUCTOR
IN H3 FOR GROUPS 8 & 9



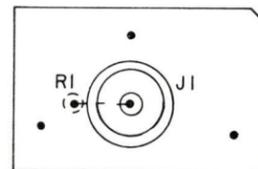
(19C327759, Rev. 1)
(19B219444, Sh. 1, Rev. 2)
(19B219444, Sh. 2, Rev. 2)

**A301A
ANT INPUT
(FLOATING GROUND)**

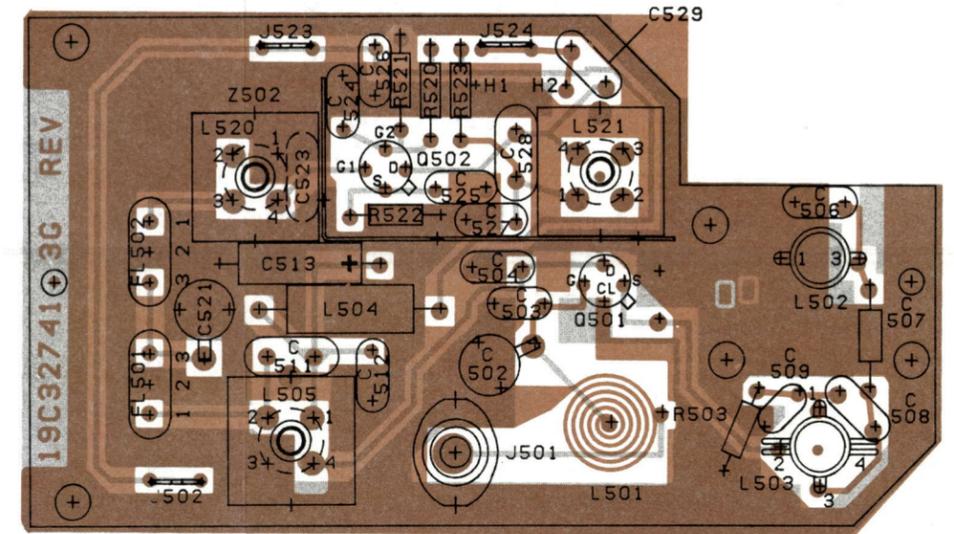


(19B219449, Sh. 1, Rev. 3)
(19B219449, Sh. 2, Rev. 3)

**A301B
ANT INPUT
(NON FLOATING GROUND)**

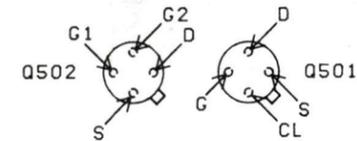


MIXER /IF BOARD



(19C327753, Rev. 0)
(19B227598, Sh. 1, Rev. 0)
(19B227598, Sh. 2, Rev. 0)

**LEAD IDENTIFICATION
FOR**

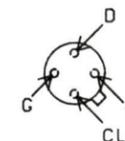


TOP VIEW

NOTE: LEAD ARRANGEMENT, AND NOT
CASE SHAPE, IS DETERMINING
FACTOR FOR LEAD IDENTIFICATION.

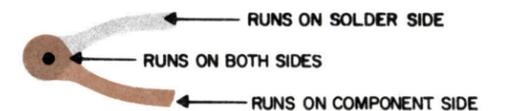
(19D429095, Rev. 1)

**LEAD IDENTIFICATION
FOR Q2**



TOP VIEW

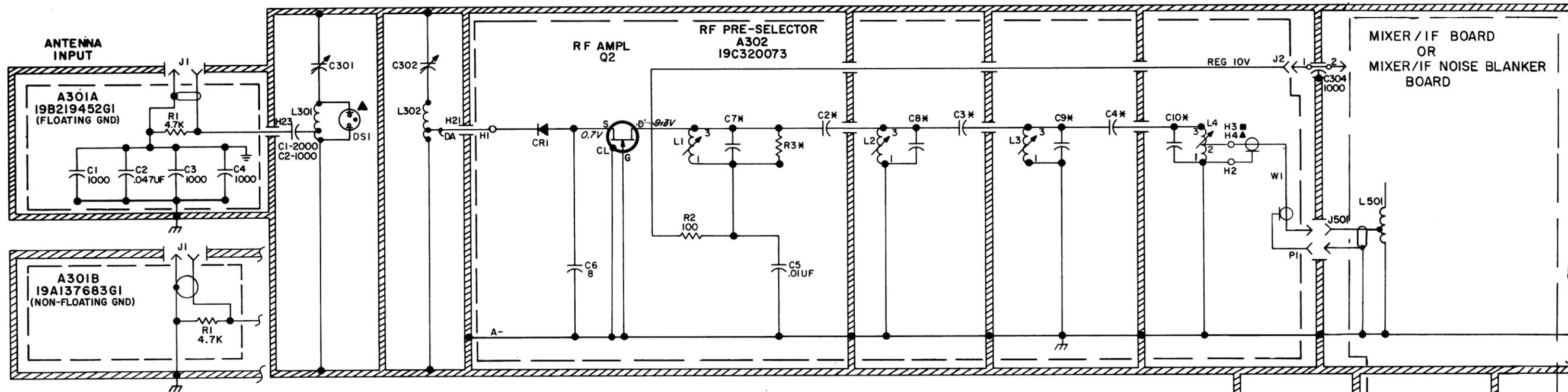
NOTE: LEAD ARRANGEMENT, AND NOT
CASE SHAPE, IS DETERMINING
FACTOR FOR LEAD IDENTIFICATION.



OUTLINE DIAGRAM

**66-88 MHz RF ASSEMBLY
AND MIXER/IF BOARD**

R F ASSEMBLY
PL19D416478



*** COMPONENT VALUE TABLE**

COMP DESIG	LL	L	M	H
RF FREQ	25-30MHZ	30-36MHZ	36-42 MHZ	42-50MHZ
IF FREQ	11.2 MHZ	9.4 MHZ	11.2 MHZ	9.4 MHZ
C2	1.0	.75	.68	.82
C3	1.0	.75	.68	.82
C4	1.0	.75	.68	.82
C7	51	39	30	18
C8	51	39	30	18
C9	51	39	30	18
C10	56	39	30	18
R3			24K	6.2K

MID BAND

*** COMPONENT VALUE TABLE**

SPLIT	ML LOW	MH HIGH
RF FREQ	66-78MHZ	77-88MHZ
IF FREQ	11.2 MHZ	11.2 MHZ
C2	.47	.39
C3	.56	.47
C4	1.0	.82
C7	15	10
C8	18	13
C9	18	13
C10	18	13
R3	6.8K	6.8K

RF ASSEMBLY	RF PRE-SELECTOR	ANTENNA INPUT	FREQ (MHZ)			
19D416478G1	C	19C320073G1	C	19B219452GI	-	25-30 (LL)
19D416478G2	C	19C320073G2	F	19B219452GI	-	30-36 (L)
19D416478G3	B	19C320073G3	E	19B219452GI	-	36-42 (M)
19D416478G4	B	19C320073G4	C	19B219452GI	-	42-50 (H)
19D416478G8	-	19C320073G8	-	19B219452GI	-	66-78 (ML)
19D416478G9	-	19C320073G9	-	19B219452GI	-	77-88 (MH)
19D416478G10	-	19C320073G1	C	19B219452GI	-	25-30 (LL)
19D416478G11	-	19C320073G2	F	19A137683GI	-	30-36 (L)
19D416478G12	-	19C320073G3	E	19A137683GI	-	36-42 (M)
19D416478G13	-	19C320073G4	C	19A137683GI	-	42-50 (H)
19D416478G14	-	19C320073G8	-	19A137683GI	-	66-78 (ML)
19D416478G15	-	19C320073G9	-	19A137683GI	-	77-88 (MH)

VOLTAGE READINGS

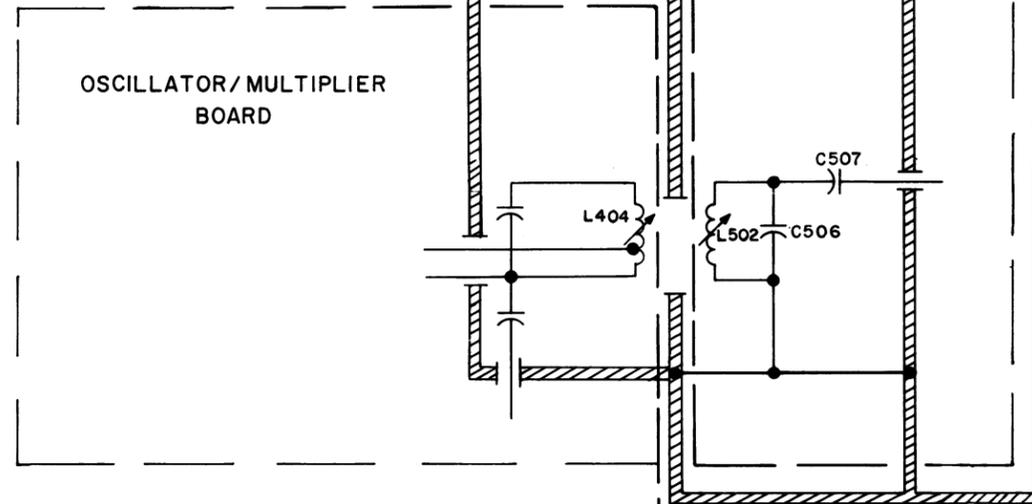
VOLTAGE READINGS ARE TYPICAL READINGS MEASURED TO SYSTEM NEGATIVE (P903-10) WITH TEST SET MODEL 4EX3A11 OR A 20,000 OHM-PER-VOLT METER.

- ⎓ INDICATES A-
- ⊥ INDICATES VEHICLE GROUND

ALL RESISTORS ARE 1/4 WATT UNLESS OTHERWISE SPECIFIED AND RESISTOR VALUES IN OHMS UNLESS FOLLOWED BY K=1000 OHMS OR MEG=1,000,000 OHMS. CAPACITOR VALUES IN PICOFARADS (EQUAL TO MICROMICROFARADS) UNLESS FOLLOWED BY UF= MICROFARADS. INDUCTANCE VALUES IN MICROHENRYS UNLESS FOLLOWED BY MH= MILLIHENRYS OR H=HENRYS.

CPD 310A

IN ORDER TO RETAIN RATED EQUIPMENT PERFORMANCE, REPLACEMENT OF ANY SERVICE PART SHOULD BE MADE ONLY WITH A COMPONENT HAVING THE SPECIFICATIONS SHOWN ON THE PARTS LIST FOR THAT PART.



SCHEMATIC DIAGRAM

66-88 MHz RF ASSEMBLY

PARTS LIST

LBI30559C

66-88 MHz
RF ASSEMBLY 19D416478G8, G14 66-78 MHz
AND
MIF ASSEMBLY 19C327413G1, G2

SYMBOL	GE PART NO.	DESCRIPTION
A301A		RF ASSEMBLY 19D416478G8, G14 66-78 MHz AND 19D416478G9, G15 77-88 MHz COMPONENT BOARD 19B219452G1 ----- CAPACITORS ----- C1 19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. C2 19A116080P5 Polyester: 0.047 μf ±20%, 50 VDCW. C3 and C4 19A116655P19 Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap. ----- JACKS AND RECEPTACLES ----- J1 19A130924G1 Connector, receptacle: coaxial, jack type; sim to Cinch 14H11613. ----- RESISTORS ----- R1 19A700106P79 Composition: 4.7K ohms ±5%, 1/4 w. A301B ANTENNA INPUT PLATE 19A137683G1 ----- JACKS AND RECEPTACLES ----- J1 7104941P20 Connector, phono: jack; sim to National Tel. ----- RESISTORS ----- R1 19A700106P79 Composition: 4.7K ohms ±5%, 1/4 w. A302 COMPONENT BOARD 19C320073G8 66-78 MHz (ML) 19C320073G9 77-88 MHz (MH) ----- CAPACITORS ----- C2ML 19A700013P9 Phenolic: 0.47 pf ±5%, 500 VDCW. C2MH 19A700013P8 Phenolic: 0.39 pf ±5%, 500 VDCW. C3ML 19A700013P10 Phenolic: 0.56 pf ±5%, 500 VDCW. C3MH 19A700013P9 Phenolic: 0.47 pf ±5%, 500 VDCW. C4ML 19A700013P13 Phenolic: 1.0 pf ±5%, 500 VDCW. C4MH 19A700013P12 Phenolic: 0.82 pf ±5%, 500 VDCW. C5 19A116080P101 Polyester: 0.01 μf ±10%, 50 VDCW. C6 19A116655P8K8 Ceramic disc: 8 pf ±1 pf ±10%, 500 VDCW, temp coef -80 PPM. C7ML 5498219P244 Ceramic disc: 15 pf ±5%, 500 VDCW, temp coef -80 PPM. C7MH 5496219P241 Ceramic disc: 10 pf ±0.25 pf, 500 VDCW, temp coef -80 PPM. C8ML 5496219P245 Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM. C8MH 5496219P243 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef -80 PPM. C9ML 5496219P245 Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM. C9MH 5496219P243 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef -80 PPM. C10ML 5496219P245 Ceramic disc: 18 pf ±5%, 500 VDCW, temp coef -80 PPM. C10MH 5496219P243 Ceramic disc: 13 pf ±5%, 500 VDCW, temp coef -80 PPM.

SYMBOL	GE PART NO.	DESCRIPTION
CR1	19A116052P2	----- DIODES AND RECTIFIERS ----- Silicon, hot carrier: Fwd. drop .410 volts max.
J2	19A116975P1	----- JACKS AND RECEPTACLES ----- Contact, electrical.
L1ML and L1MH	19C307170P303	----- INDUCTORS ----- Coil, RF: variable; sim to Paul Smith 071774-OG-6.
L2ML and L2MH	19C307170P303	Coil, RF: variable; sim to Paul Smith 071774-OG-6.
L3ML and L3MH	19C307170P303	Coil, RF: variable; sim to Paul Smith 071774-OG-6.
L4ML and L4MH	19C307170P310	Coil, RF: variable; sim to Paul Smith 060876-DB-1.
P1		----- PLUGS ----- (Part of W1).
Q2	19A116960P1	----- TRANSISTORS ----- N Type, field effect; sim to Type 2M4416.
R2	19A700106P39	----- RESISTORS ----- Composition: 100 ohms ±5%, 1/4 w.
R3ML and R3MH	19A700106P83	Composition: 6.8K ohms ±10%, 1/4 w.
W1	5491689P85	----- CABLES ----- Cable, RF: approx 4 inches long. (Includes P1).
C304	19B209488P2	----- CAPACITORS ----- Ceramic, feed-thru: 1000 pf ±100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.
C305	19B209488P1	Ceramic, feed-thru: 6.8 pf ±20%, 500 VDCW; sim to Allen-Bradley Style FA5D.
C306	19B209488P2	Ceramic, feed-thru: 1000 pf ±100 -0%, 500 VDCW; sim to Allen-Bradley Style FA5D.
L301ML	19B219455G5	----- INDUCTORS ----- Coil. Includes:
C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C301	19B209159P5	Capacitor, variable, air: 1.60-3.8 pf, 650 v peak; sim to EF Johnson 189.
L301MH	19B219455G7	Coil. Includes:
C2	5494481P11	Capacitor, ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
C301	19B209159P5	Capacitor, variable, air: 1.60-3.8 pf, 650 v peak; sim to EF Johnson 189.
L302ML	19B219455G6	Coil. Includes:
C302	19B209159P5	Capacitor, variable, air: 1.60-3.8 pf, 650 v peak; sim to EF Johnson 189.
L302MH	19B219455G8	Coil. Includes:
C302	19B209159P5	Capacitor, variable, air: 1.60-3.8 pf, 650 v peak; sim to EF Johnson 189.
	19B201074P305	----- MISCELLANEOUS ----- Tap screw, Phillips POZIDRIV®: No. 6-32 x 5/16. (Secures cover- Quantity 7).
	19B209209P306	Tap screw, Phillips POZIDRIV®: No. 6-32 x 3/8. (Secures cover- Quantity 6).
	19B219451P1	Cover.
	19E500959G1	Casting.

SYMBOL	GE PART NO.	DESCRIPTION
C502	19A700012P2	MIF ASSEMBLY 19C327413G1 66-78 MHz (L) 19C327413G2 77-88 MHz (H) ----- CAPACITORS ----- Variable, ceramic: 2.5 to 20 pf, 200 VDCW, temp coef -250 to -700 Parts/M°C; sim to Panasonic ECV-12W20X32.
C503	19A116656P10J0	Ceramic disc: 10 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
C503H	19A116656P8J0	Ceramic disc: 8 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM.
C504	19A116656P22J0	Ceramic disc: 22 pf ±5%, 500 VDCW, temp coef 0 PPM.
C506L	19A116656P27K8	Ceramic disc: 27 pf ±10%, 500 VDCW, temp coef -80 PPM.
C506H	19A116656P20J8	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -80 PPM.
C507L	19A700013P12	Phenolic: 0.82 pf ±5%, 500 VDCW.
C507H	19A700013P11	Phenolic: 0.68 pf ±5%, 500 VDCW.
C508L	19A116656P27K8	Ceramic disc: 27 pf ±10%, 500 VDCW, temp coef -80 PPM.
C508H	19A116656P20J8	Ceramic disc: 20 pf ±5%, 500 VDCW, temp coef -80 PPM.
C509	19A116080P101	Polyester: 0.01 μf ±10%, 50 VDCW.
C511	5490008P137	Silver mica: 270 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C512	19A116080P3	Polyester: 0.022 μf ±20%, 50 VDCW.
C513	5496267P10	Tantalum: 22 μf ±20%, 15 VDCW; sim to Sprague Type 150D.
C521	19A700012P1	Variable, ceramic: 2 to 10 pf, 200 VDCW, temp coef -350 +500 Parts/M°C; sim to Panasonic ECV-12W10X32. (Part of Z502).
C523		
C524 thru C527	19A116080P3	Polyester: 0.022 μf ±20%, 50 VDCW.
C528	5490008P139	Silver mica: 330 pf ±10%, 500 VDCW; sim to Electro Motive Type DM-15.
C529	19A116655P19	Ceramic disc: 1000 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.
FL501	19B219573G3	----- FILTERS ----- Crystal, freq: Sec 1: Resonator A: 11,204000 KHz, Resonator B: 11,196000 KHz. Sec 2: Resonator A: 11,204000 KHz, Resonator B: 11,196000 KHz.
FL502		(Part of FL501).
J501	19A130924G1	----- JACKS AND RECEPTACLES ----- Receptacle, coaxial: jack type; sim to Cinch 14H11613.
J502	19A116975P1	Contact, electrical.
J523 and J524	19A116975P1	Contact, electrical.
L501		----- INDUCTORS ----- (Part of printed board 19C327412P1).
L502	19C307169P201	Coil, RF, variable: sim to Paul Smith 091774-W5-1.
L503	19C307169P206	Coil, RF, variable: sim to Paul Smith 060876-DB-3.
L504	7488079P48	Choke, RF: 27.0 μh ±10%, 1.40 ohms DC res max; sim to Jeffers 4422-9K.
L505	19C320141G30	Coil. Includes: Tuning slug.
L520	5493185P9	(Part of Z502).
L521	19C320141G6	Coil. Includes: Tuning slug.

SYMBOL	GE PART NO.	DESCRIPTION
Q501	19A116960P1	----- TRANSISTORS ----- N Type, field effect; sim to Type 2M4416.
Q502	19A116818P1	N Channel, field effect.
R503	19A700106P67	----- RESISTORS ----- Composition: 1.5K ohms ±10%, 1/4 w.
R520	19A700106P87	Composition: 10K ohms ±10%, 1/4 w.
R521	19A700106P77	Composition: 3.9K ohms ±5%, 1/4 w.
R522	19A700106P47	Composition: 220 ohms ±5%, 1/4 w.
R523	19A700106P31	Composition: 47 ohms ±5%, 1/4 w.
Z502	19C320141G20	----- NETWORKS ----- Coil. Includes: Tuning slug.
	5493185P9	
	19B219470P2	Shield.
	19A129424G1	Can. (Used with L505, L520, L521).
	4031594P1	Insulator. (Used with C502, C521).

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter," which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- REV. A-E - RF Pre-Selector 19C320073G2
Incorporated in initial shipment.
- REV. F - To improve RF Sensitivity. Deleted R3L.